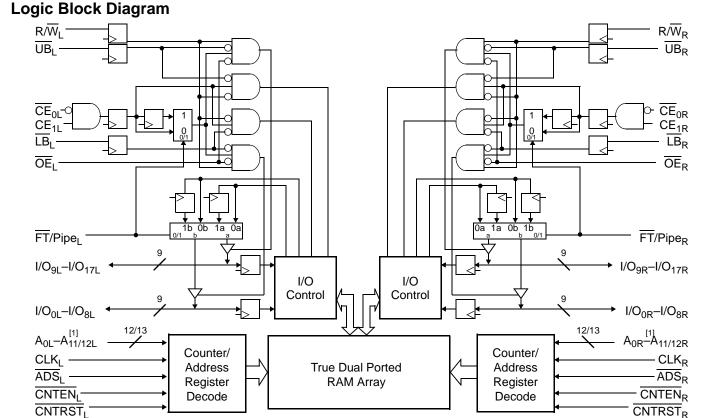


3.3 V 4 K/8 K x 18 Synchronous Dual Port Static RAM

Features

- True dual ported memory cells which allow simultaneous access of the same memory location
- Two flow-through/pipelined devices
 - □ 4 K x 18 organization (CY7C09349AV)
 - 8 K x 18 organization (CY7C09359AV)
- Three modes
 - □ Flow-through
 - □ Pipelined
 - □ Burst
- Pipelined output mode on both ports allows fast 67-MHz operation
- 0.35-micron complementary metal oxide semiconductor (CMOS) for optimum speed/power

- High-speed clock to data access 9 and 12 ns (max)
- 3.3 V low operating power
 - ☐ Active = 135 mA (typical)
 - □ Standby = 10 µA (typical)
- Fully synchronous interface for easier operation
- Burst counters increment addresses internally
 - □ Shorten cycle times
 - □ Minimize bus noise
 - Supported in flow-through and pipelined modes
- Dual chip enables for easy depth expansion
- Upper and lower byte controls for bus matching
- Automatic power-down
- Available in 100-pin thin quad flat pack (TQFP)
 For a complete list of related documentation, click here.



Note

A₀-A₁₁ for 4 K; A₀-A₁₂ for 8 K devices.



Functional Description

The CY7C09349AV and CY7C09359AV are high-speed 3.3 V synchronous CMOS 4 K and 8 K x 18 dual-port static RAMs. Two ports are provided, permitting independent, simultaneous access for reads and writes to any location in memory. [2] Registers on control, address, and data lines allow for minimal set-up and hold times. In pipelined output mode, data is registered for decreased cycle time. Clock to data valid $t_{CD2} = 9~{\rm ns}$ (pipelined). Flow-through mode can also be used to bypass the pipelined output register to eliminate access latency. In flow-through mode data will be available $t_{CD1} = 20~{\rm ns}$ after the address is clocked into the device. Pipelined output or flow-through mode is selected via the FT/Pipe pin.

Each port contains a burst counter on the input address register. The internal write pulse width is independent of the LOW-to-HIGH transition of the clock signal. The internal write pulse is self-timed to allow the shortest possible cycle times.

A HIGH on $\overline{\text{CE}}_0$ or LOW on CE_1 for one clock cycle will power down the internal circuitry to reduce the static power consumption. The use of multiple chip enables allows easier banking of multiple chips for depth expansion configurations. In the pipelined mode, one cycle is required with $\overline{\text{CE}}_0$ LOW and $\overline{\text{CE}}_1$ HIGH to reactivate the outputs.

Counter enable inputs are provided to stall the operation of the address input and utilize the internal address generated by the internal counter for fast interleaved memory applications. A port's burst counter is loaded with the port's address strobe (ADS). When the port's count enable (CNTEN) is asserted, the address counter will increment on each LOW-to-HIGH transition of that port's clock signal. This will read/write one word from/into each successive address location until CNTEN is deasserted. The counter can address the entire memory array and will loop back to the start. Counter reset (CNTRST) is used to reset the burst counter.

All parts are available in 100-pin thin quad plastic flatpack (TQFP) packages.

Note

^{2.} When simultaneously writing to the same location, final value cannot be guaranteed.



Contents

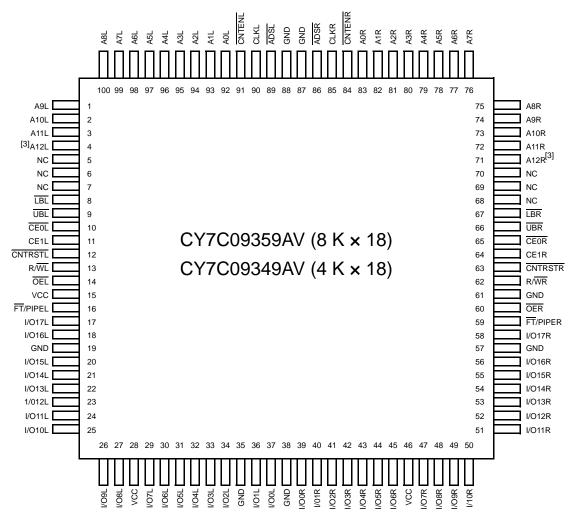
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4 K x 18 3.3 V Synchronous Dual-Port SRAM	

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Pin Configuration

Figure 1. 100-pin TQFP (Top View)



Selection Guide

	CY7C09349AV CY7C09359AV -9	CY7C09349AV -12
f _{MAX2} (MHz) (pipelined)	67	50
Max access time (ns) (clock to data, pipelined)	9	12
Typical operating current I _{CC} (mA)	135	115
Typical standby current for I _{SB1} (mA) (both ports TTL level)	20	20
Typical standby current for I _{SB3} (μA) (both ports CMOS level)	10	10

Note

3. This pin is NC for CY7C09349AV.



Pin Definitions

Left Port	Right Port	Description
A _{0L} -A _{12L}	A _{0R} -A _{12R}	Address inputs (A ₀ –A ₁₁ for 4 K, A ₀ –A ₁₂ for 8 K devices).
ADS _L	ADS _R	Address strobe input. Used as an address qualifier. This signal should be asserted LOW during normal read or write transactions. Asserting this signal LOW also loads the burst address counter with data present on the I/O pins.
CE _{0L} , CE _{1L}	CE _{0R} , CE _{1R}	Chip enable input. To select either the left or right port, both \overline{CE}_0 and CE_1 must be asserted to their active states ($\overline{CE}_0 \le V_{IL}$ and $CE_1 \ge V_{IH}$).
CLK _L	CLK _R	Clock signal. This input can be free running or strobed. Maximum clock input rate is f _{MAX} .
CNTENL	CNTEN _R	Counter enable input. Asserting this signal L <u>OW increments the burst address counter of its respective port on each rising edge of CLK. CNTEN is disabled if ADS or CNTRST are asserted LOW.</u>
CNTRSTL	CNTRST _R	Counter reset input. Asserting this signal LOW resets the burst address counter of its respective port to zero. CNTRST is not disabled by asserting ADS or CNTEN.
I/O _{0L} –I/O _{17L}	I/O _{0R} –I/O _{17R}	Data bus input/output (I/O ₀ -I/O ₁₅ for ×16 devices).
LB _L	LB _R	Lower byte select input. Asserting this signal LOW enables read and write operations to the lower byte $(I/O_0-I/O_8)$ for x18, $I/O_0-I/O_7$ for x16) of the memory array. For read operations both the LB and OE signals must be asserted to drive output data on the lower byte of the data pins.
UB _L	UB _R	Upper byte select input. Same function as $\overline{\text{LB}}$, but to the upper byte (I/O _{8/9L} -I/O _{15/17L}).
OE _L	ŌĒ _R	Output enable input. This signal must be asserted LOW to enable the I/O data pins during read operations.
R/W _L	R/W _R	Read/write enable input. This signal is asserted LOW to write to the dual port memory array. For read operations, assert this pin HIGH.
FT/PIPE _L	FT/PIPE _R	Flow-through/pipelined select input. For flow-through mode operation, assert this pin LOW. For pipelined mode operation, assert this pin HIGH.
GND	•	Ground input.
NC		No connect.
V _{CC}		Power input.

Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. User guidelines are not tested.

Storage temperature....... -65 °C to +150 °C Ambient temperature with power applied .-55 °C to +125 °C Supply voltage to ground potential-0.5 V to +4.6 V DC voltage applied to outputs in high Z state-0.5 V to V_{CC} + 0.5 V DC input voltage-0.5 V to V_{CC} + 0.5 V

Output current into outputs (LOW)	20 mA
Static discharge voltage	> 2001 V
Latch-up current	> 200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0 °C to +70 °C	$3.3 \text{ V} \pm 300 \text{ mV}$
Industrial	–40 °C to +85 °C	3.3 V ± 300 mV



Electrical Characteristics

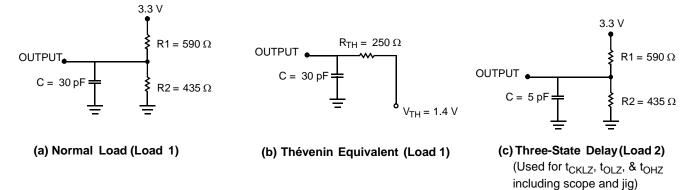
Over the Operating Range

			CY7C09349AV CY7C09359AV						
Parameter	Description		-9			-12		Unit	
		Min	Тур	Max	Min	Тур	Max		
V _{OH}	Output HIGH voltage ($V_{CC} = Min, I_{OH} = -4$.	0 mA)	2.4	_	_	2.4	-	_	V
V _{OL}	Output LOW voltage (V _{CC} = Min, I _{OH} = +4.0	0 mA)	_		0.4	_		0.4	V
V _{IH}	Input HIGH voltage		2.0		_	2.0		_	V
V _{IL}	Input LOW voltage	_		0.8	_		0.8	V	
I _{OZ}	Output leakage current	-10		10	-10		10	μA	
I _{CC}	Operating current (V _{CC} = Max,	Commercial	-	135	230	_	115	180	mA
	I _{OUT} = 0 mA) outputs disabled	Industrial		-	_		155	250	mA
I _{SB1}	Standby current (both ports TTL level) ^[4]	Commercial		20	75		20	70	mA
	CE_L and $CE_R \ge V_{IH}$, $f = f_{MAX}$	Industrial		-	_		30	80	mA
I _{SB2}	Standby current (one port TTL level)[4]	Commercial		95	155		85	140	mA
	CE_L or $CE_R \ge V_{IH}$, $f = f_{MAX}$	Industrial		_			95	150	mA
I _{SB3}	Standby current (both ports CMOS level) ^[4]	Commercial		10	500		10	500	μA
	CE_L and $CE_R \ge V_{CC} - 0.2 \text{ V, f} = 0$	Industrial		-	_		10	500	μA
I _{SB4}	Standby current (one port CMOS level) ^[4]	Commercial		85	115	•	75	100	mA
	CE_L or $CE_R \ge V_{IH}$, $f = f_{MAX}$	Industrial	•	-	-	•	85	110	mA

Capacitance

Parameter	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz},$	10	pF
C _{OUT}	Output capacitance	$V_{CC} = 3.3 \text{ V}$	10	pF

AC Test Loads



Document Number: 001-63888 Rev. *C



Switching Characteristics

Over the Operating Range

			CY7C09			
		-	9	-12		
Parameter	Description	Min	Max	Min	Max	Unit
f _{MAX1}	f _{Max} flow-through	_	40	_	33	MHz
f _{MAX2}	f _{Max} pipelined	-	67	_	50	MHz
t _{CYC1}	Clock cycle time – flow-through	25	_	30	_	ns
t _{CYC2}	Clock cycle time – pipelined	15	_	20	_	ns
t _{CH1}	Clock HIGH time – flow-through	12	_	12	_	ns
t _{CL1}	Clock LOW time – flow-through	12	_	12	_	ns
t _{CH2}	Clock HIGH time – pipelined	6	_	8	_	ns
t _{CL2}	Clock LOW time – pipelined	6	_	8	_	ns
t _R	Clock rise time	_	3	_	3	ns
t _F	Clock fall time	_	3	_	3	ns
t _{SA}	Address set-up time	4	_	4	_	ns
t _{HA}	Address hold time	1	_	1	_	ns
t _{SC}	Chip enable set-up time	4	_	4	_	ns
t _{HC}	Chip enable hold time	1	_	1	_	ns
t _{SW}	R/W set-up time	4	_	4	_	ns
t _{HW}	R/W hold time	1	_	1	_	ns
t _{SD}	Input data set-up time	4	_	4	_	ns
t _{HD}	Input data hold time	1	_	1	_	ns
t _{SAD}	ADS set-up time	4	_	4	_	ns
t _{HAD}	ADS hold time	1	_	1	_	ns
t _{SCN}	CNTEN set-up time	4	_	4	_	ns
t _{HCN}	CNTEN hold time	1	_	1	_	ns
t _{SRST}	CNTRST set-up time	4	_	4	_	ns
t _{HRST}	CNTRST hold time	1	_	1	_	ns
t _{OE}	Output enable to data valid	_	10	_	12	ns
t _{OLZ}	OE to low Z	2	_	2	_	ns
t _{OHZ}	OE to high Z	1	7	1	7	ns
t _{CD1}	Clock to data valid – flow-through	_	20	_	25	ns
t _{CD2}	Clock to data valid – pipelined	_	9	_	12	ns
t _{DC}	Data output hold after clock HIGH	2	_	2	_	ns
t _{CKHZ}	Clock HIGH to output high Z	2	9	2	9	ns
t _{CKLZ}	Clock HIGH to output low Z	2	_	2	_	ns
Port to por	t delays	l	1	1	1	1
t _{CWDD}	Write port clock HIGH to read data delay	_	40	_	40	ns
t _{CCS}	Clock to clock set-up time	_	15	_	15	ns



Switching Waveforms

Figure 2. Read Cycle for Flow-through Output ($\overline{\text{FT}}/\text{PIPE} = V_{IL}$)[5, 6, 7, 8]

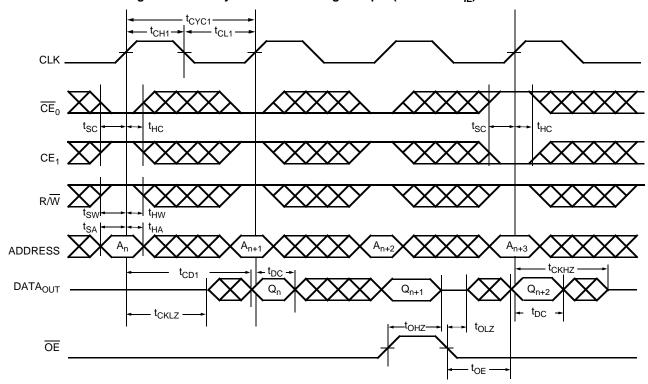
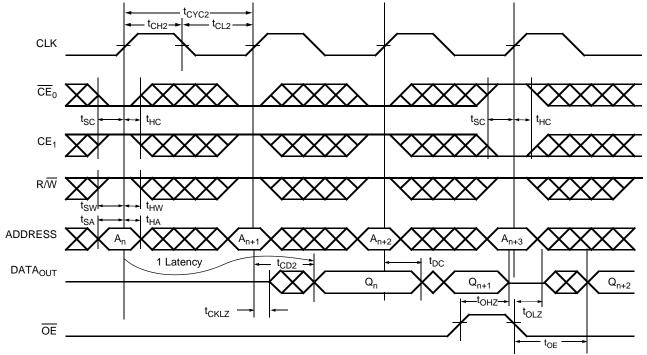


Figure 3. Read Cycle for Pipelined Operation ($\overline{\text{FT}}/\text{PIPE} = V_{\text{IH}})^{[5, \, 6, \, 7, \, 8]}$



- OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.

 ADS = V_{IL}, CNTEN and CNTRST = V_{IH}.

- The output is disabled (high-impedance state) by $\overline{CE}_0 = V_{IL}$ or $CE_1 = V_{IL}$ following the next rising edge of the clock. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK. Numbers are for reference only.

 t_{CKLZ}

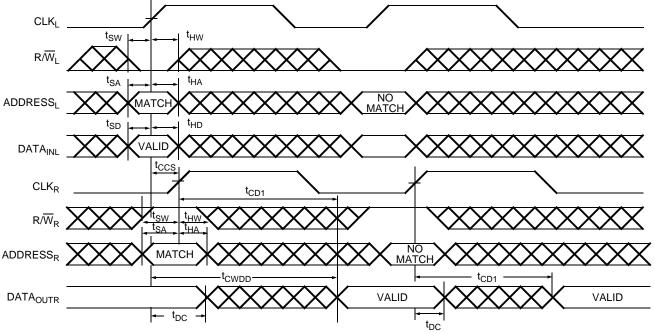


Switching Waveforms (continued)

Figure 4. Bank Select Pipelined Read^[9, 10] t_{CYC2} CLK_L $t_{\text{HA}} \\$ t_{SA} $\mathsf{ADDRESS}_{(\mathsf{B1})}$ D_3 DATA_{OUT(B1)} ADDRESS_(B2) t_{CD2} DATA_{OUT(B2)}

Figure 5. Left Port Write to Flow-through Right Port Read^[11, 12, 13, 14]

t_{CKLZ}



Notes

- Notes

 9. In this depth expansion example, B1 represents Bank #1 and B2 is Bank #2; Each bank consists of one Cypress dual-port device from this data sheet.

 ADDRESS_(B1) = ADDRESS_(B2).

 10. UB, LB, OE and ADS = V_{IL}; CE₁(B1), CE₁(B2), R/W, CNTEN, and CNTRST = V_{IH}.

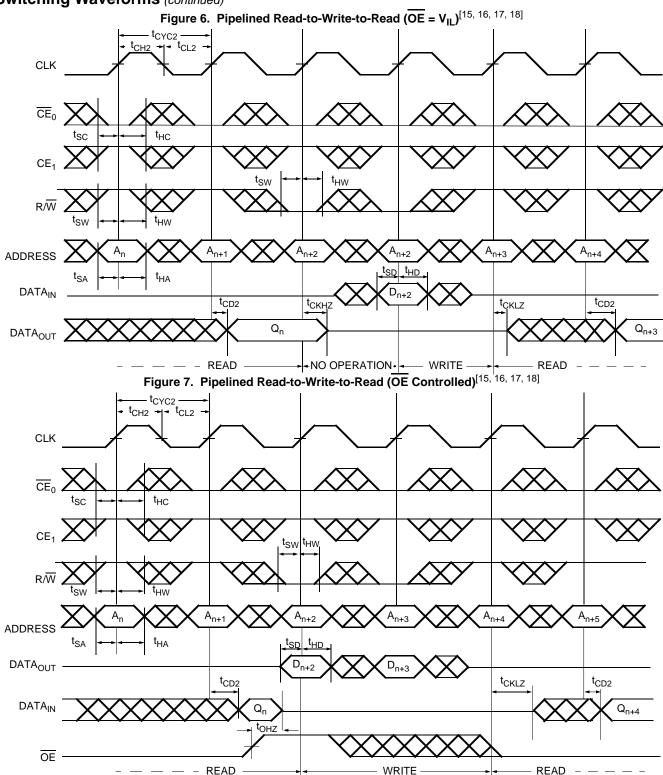
 11. The same waveforms apply for a right port write to flow-through left port read.

 12. CE₀, UB, LB, and ADS = V_{IL}; CE₁, CNTEN, and CNTRST = V_{IH}.

 13. OE = V_{IL} for the right port, which is being read from. OE = V_{IH} for the left port, which is being written to.

 14. If t_{CCS} ≤ maximum specified, then data from right port READ is not valid until the maximum specified for t_{CWDD}. If t_{CCS} > maximum specified, then data is not valid until t_{CCS} + t_{CD1}. t_{CWDD} does not apply in this case.





- 15. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK. Numbers are for reference only.

- 16. Output state (HIGH, LOW, or high-impedance) is determined by the previous cycle control signals.

 17. CE₀ and ADS = V_{IL}; CE₁, CNTEN, and CNTRST = V_{IH}.

 18. During "No operation", data in memory at the selected address may be corrupted and should be rewritten to ensure data integrity.



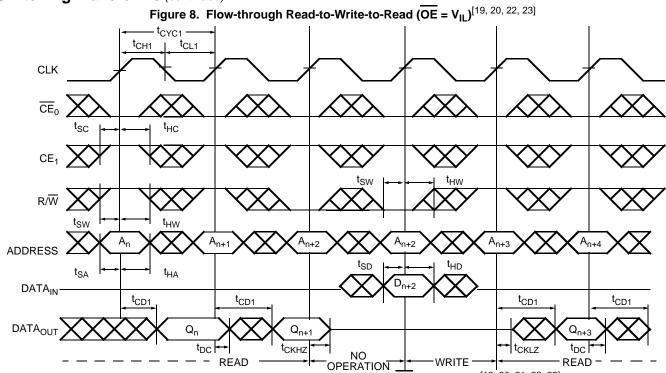
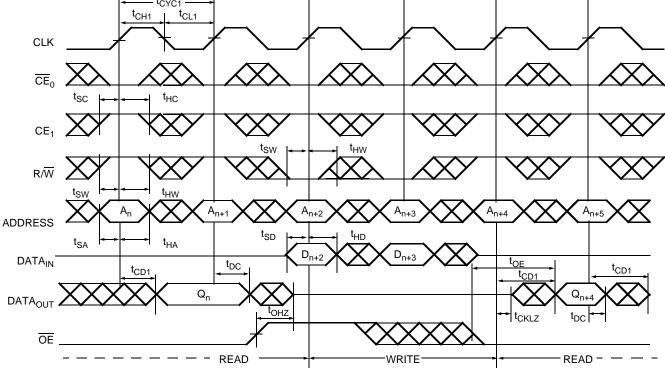


Figure 9. Flow-through Read-to-Write-to-Read (OE Controlled)[19, 20, 21, 22, 23]



- Notes

 19. ADS = V_{IL}, CNTEN and CNTRST = V_{IH}.

 20. Addresses do not have to be accessed sequentially since ADS = V_{IL} constantly loads the address on the rising edge of the CLK. Numbers are for reference only.

 21. Output state (HIGH, LOW, or high-impedance) is determined by the previous cycle control signals.

 22. CE₀ and ADS = V_{IL}; CE₁, CNTEN, and CNTRST = V_{IH}.

 23. During "No operation," data in memory at the selected address may be corrupted and should be rewritten to ensure data integrity.



Figure 10. Pipelined Read with Address Counter Advance [24]

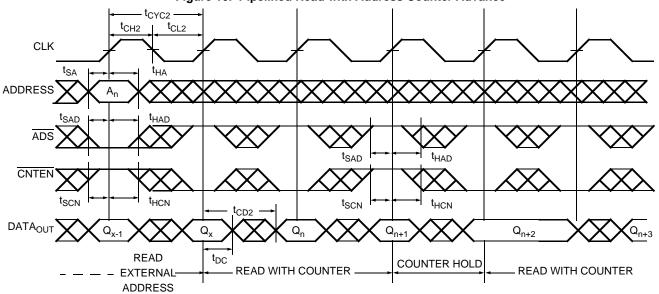


Figure 11. Flow-through Read with Address Counter Advance^[24]

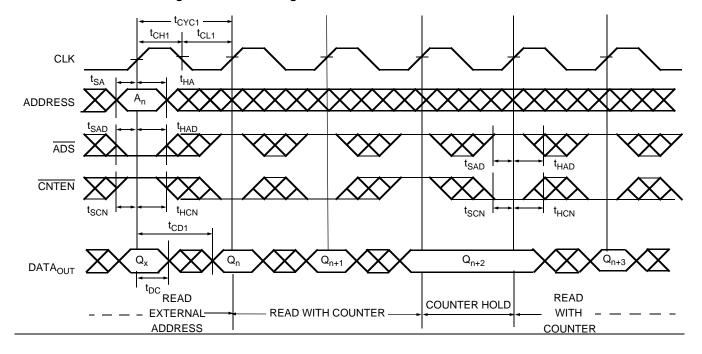
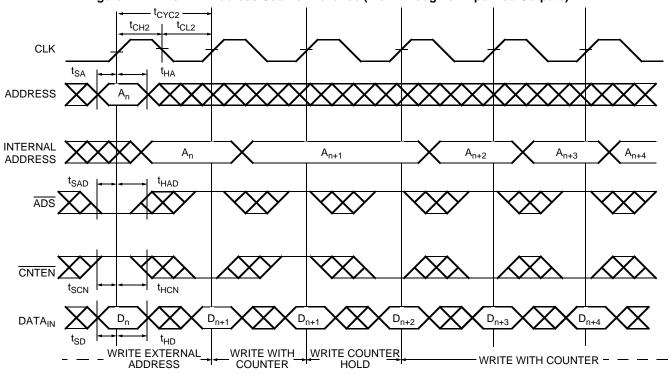




Figure 12. Write with Address Counter Advance (Flow-through or Pipelined Outputs)^[25, 26]

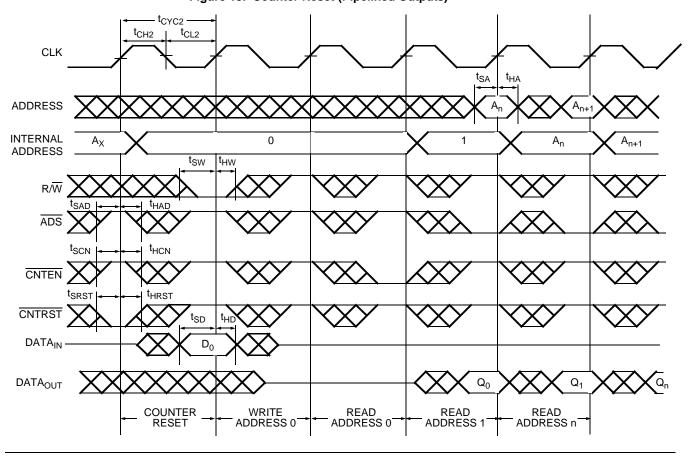


^{25.} $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$.

26. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = V_{IL}$ and equals the counter output when $\overline{ADS} = V_{IH}$.



Figure 13. Counter Reset (Pipelined Outputs) $^{[27,\,28,\,29,\,30]}$



^{27.} Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{|L}$ constantly loads the address on the rising edge of the CLK. Numbers are for reference only. 28. Output state (HIGH, LOW, or high-impedance) is determined by the previous cycle control signals.

^{29.} CE₀, UB, and LB = V_{IL}: CE₁ = V_{IH}.

30. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset.



Read/Write and Enable Operation[31, 32, 33]

		Inputs		Outputs		
OE	CLK	CE ₀	CE ₁	R/W	I/O ₀ -I/O ₁₇	Operation
Х	7	Н	Х	Х	High Z	Deselected ^[34]
Х		Х	L	Х	High Z	Deselected ^[34]
Х		L	Н	L	D _{IN}	Write
L		L	Н	Н	D _{OUT}	Read ^[34]
Н	Х	L	Н	Х	High Z	Outputs disabled

Address Counter Control Operation[31, 35, 36, 37]

Address	Previous Address	CLK	ADS	CNTEN	CNTRST	1/0	Mode	Operation
Х	Х		Х	Х	L	D _{out(0)}	Reset	Counter reset to address 0
A _n	Х		L	Х	Н	D _{out(n)}	Load	Address load into counter
Х	A _n	4	Н	Н	Н	D _{out(n)}	Hold	External address blocked—counter disabled
Х	A _n		Н	L	Н	D _{out(n+1)}	Increment	Counter enabled—internal address generation

Notes

^{31. &}quot;X" = "<u>Don't Care,"</u> "H" = V_{IH}, "L" = V_{IL}. 32. <u>ADS, CNTEN, CNTRST</u> = "Don't Care."

^{33.} OE is an asynchronous input signal.

34. When CE changes state in the pipelined mode, deselection and read happen in the following clock cycle.

35. CE₀ and OE = V_{IL}; CE₁ and R/W = V_{IH}.

36. Data shown for flow-through mode; pipelined mode output will be delayed by one cycle.

37. Counter operation is independent of CE₀ and CE₁.

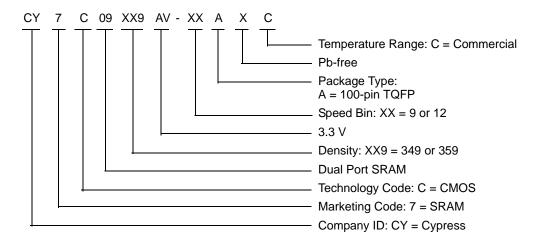


Ordering Information

4 K × 18 3.3 V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
9	CY7C09349AV-9AXC	A100	100-pin Pb-free Thin Quad Flat Pack	Commercial
12	CY7C09349AV-12AXC	A100	100-pin Pb-free Thin Quad Flat Pack	Commercial

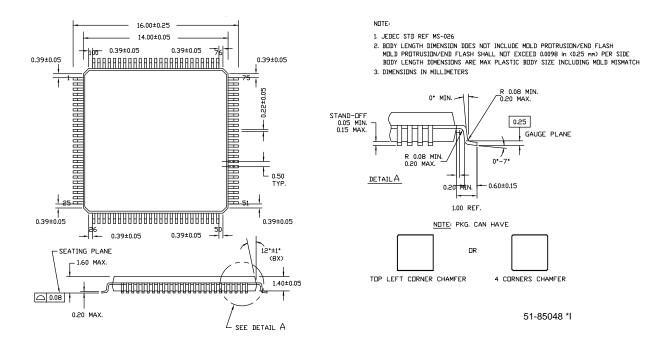
Ordering Code Definitions





Package Diagram

Figure 14. 100-pin TQFP (14 × 14 × 1.4 mm) A100SA Package Outline, 51-85048





Acronyms

Acronym	Description	
CE	chip enable	
CLK	clock	
CMOS	complementary metal oxide semiconductor	
I/O	Input/output	
OE	output enable	
SRAM	static random access memory	
TQFP	thin quad flat pack	

Document Conventions

Units of Measure

Symbol	Unit of Measure		
°C	degree Celsius		
MHz	megahertz		
μA	microamperes		
mA	milliamperes		
mV	millivolts		
mW	milliwatts		
ns	nanoseconds		
pF	picofarad		
V	volts		
W	watts		



Document History Page

Document Title: CY7C09349AV/CY7C09359AV, 3.3 V 4 K/8 K × 18 Synchronous Dual Port Static RAM Document Number: 001-63888						
Rev.	ECN No.	Issue Date	Orig. of Change	Description of Change		
**	2998931	09/16/2010	RAME	New data sheet.		
*A	3386551	09/28/2011	ADMU	Updated footnotes. Updated Package Diagram.		
*B	4547288	10/21/2014	ADMU	Updated Ordering Information: Updated part numbers. Updated Package Diagram: spec 51-85048 – Changed revision from *E to *I. Updated to new template.		
*C	4580426	11/25/2014	ADMU	Added related documentation hyperlink in page 1.		



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CY6116A-35DMB CY7C1049GN-10VXI CY7C128A-45DMB GS8161Z36DD-200I GS88237CB-200I RMLV0408EGSB-4S2#AA0

IDT70V5388S166BG IS64WV3216BLL-15CTLA3 IS66WVE4M16ECLL-70BLI PCF8570P K6F2008V2E-LF70000 K6T4008C1B-GB70

CY7C1353S-100AXC AS6C8016-55BIN AS7C164A-15PCN 515712X IDT71V67603S133BG IS62WV51216EBLL-45BLI

IS63WV1288DBLL-10HLI IS66WVE2M16ECLL-70BLI 70V639S10BCG IS66WVE4M16EALL-70BLI IS62WV6416DBLL-45BLI

IS61WV102416DBLL-10TLI CY7C1381KV33-100AXC CY7C1381KVE33-133AXI 8602501XA 5962-3829425MUA 5962-3829430MUA

5962-8855206YA 5962-8866201YA 5962-8866204TA 5962-8866206MA 5962-8866208UA 5962-8872502XA 5962-9062007MXA 5962
9161705MXA 70V3579S6BFI GS882Z18CD-150I M38510/28902BVA 8413202RA 5962-8866203YA 5962-8871203XA 5962
8971202ZA 5962-8872501LA 5962-8866208YA 5962-8866205YA 5962-8866205UA 5962-8866203YA 5962-8855202YA